

# KSP8098/8099

# **Amplifier Transistor**

- Collector-Emitter Voltage: V<sub>CEO</sub>= KSP8098: 60V KSP8099: 80V
- Collector Power Dissipation: P<sub>C</sub> (max)=625mW
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



## 1. Emitter 2. Base 3. Collector

# **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

| Symbol                                     | Parameter                   | Value     | Units |
|--|-----------------------------|-----------|-------|
| V <sub>CBO</sub>                           | Collector-Base Voltage      |           |       |
|  | : KSP8098                   | 60        | V     |
|  | : KSP8099                   | 80        | V     |
| V <sub>CEO</sub> Collector-Emitter Voltage |                             |           |       |
|  | : KSP8098                   | 60        | V     |
|  | : KSP8099                   | 80        | V     |
| V <sub>EBO</sub>                           | Emitter-Base Voltage        | 6         | V     |
| I <sub>C</sub>                             | Collector Current           | 500       | mA    |
| P <sub>C</sub>                             | Collector Power Dissipation | 625       | mW    |
| T <sub>J</sub>                             | Junction Temperature        | 150       | °C    |
| T <sub>STG</sub>                           | Storage Temperature         | -55 ~ 150 | °C    |

# $\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

| Symbol                | Parameter   | Test Condition  | Min.             | Max.       | Units    |
|-----------------------|---|---|------------------|------------|----------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage<br>: KSP8098                   | I <sub>C</sub> =100μA, I <sub>E</sub> =0  | 60               |            | ٧        |
| 5)./                  | : KSP8099   |   | 80               |            | V        |
| BV <sub>CEO</sub>     | * Collector-Emitter Breakdown Voltage<br>: KSP8098<br>: KSP8099 | I <sub>C</sub> =10mA, I <sub>B</sub> =0   | 60<br>80         |            | V        |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage                                  | I <sub>E</sub> =10μA, I <sub>C</sub> =0   | 6                |            | V        |
| I <sub>CBO</sub>      | Collector Cut-off Current                                       |   |                  |            | _        |
| СВО                   | : KSP8098<br>: KSP8099  | V <sub>CB</sub> =60V, I <sub>E</sub> =0<br>V <sub>CB</sub> =80V, I <sub>E</sub> =0  |                  | 100<br>100 | nA<br>nA |
| I <sub>CEO</sub>      | Collector Cut-off Current                                       | V <sub>CE</sub> =60V, I <sub>B</sub> =0   |                  | 100        | nA       |
| I <sub>EBO</sub>      | Emitter Cut-off Current   | V <sub>EB</sub> =6V, I <sub>C</sub> =0  |                  | 100        | nA       |
| h <sub>FE</sub>       | DC Current Gain   | V <sub>CE</sub> =5V, I <sub>C</sub> =1mA<br>V <sub>CE</sub> =5V, I <sub>C</sub> =10mA<br>V <sub>CE</sub> =5V, I <sub>C</sub> =100mA | 100<br>100<br>75 | 300        |          |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage                            | I <sub>C</sub> =100mA, I <sub>B</sub> =5mA<br>I <sub>C</sub> =100mA, I <sub>B</sub> =10mA   |                  | 0.4<br>0.3 | V<br>V   |
| V <sub>BE</sub> (on)  | * Base-Emitter On Voltage<br>: KSP8098<br>: KSP8099             | $V_{CE}$ =5V, $I_{C}$ =1mA<br>$V_{CE}$ =5V, $I_{C}$ =10mA   | 0.5<br>0.6       | 0.7<br>0.8 | V        |
| f <sub>T</sub>        | Current Gain Bandwidth Product                                  | V <sub>CE</sub> =5V, I <sub>C</sub> =10mA<br>f=100MHz   | 150              |            | MHz      |
| C <sub>ob</sub>       | Output Capacitance  | V <sub>CB</sub> =5V, I <sub>E</sub> =0<br>f=1MHz  |                  | 6          | pF       |

# **Typical Characteristics**

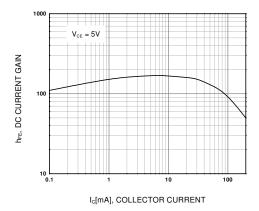


Figure 1. DC current Gain

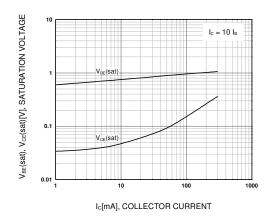


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

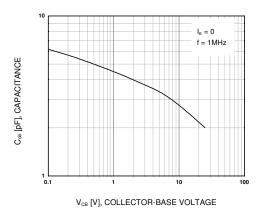


Figure 3. Output Capacitance

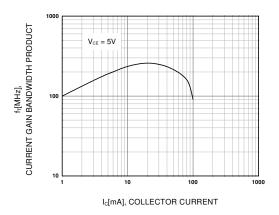
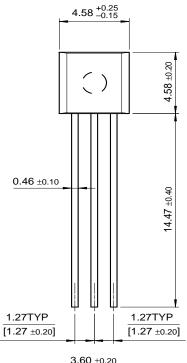
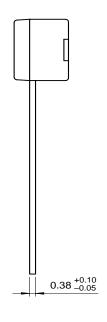
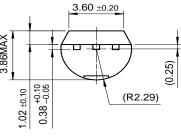


Figure 4. Current Gain Bandwidth Product

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